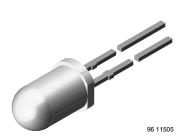
COMPLIANT HALOGEN

FREE



High Power Infrared Emitting Diode, Vishay Semiconductors 940 nm, GaAlAs/GaAs



DESCRIPTION

TSAL5300 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

FEATURES

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5

· Leads with stand-off

• Peak wavelength: $\lambda_p = 940 \text{ nm}$

High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity: $\varphi = \pm 22^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

• Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- · Infrared source for optical counters and card readers

PRODUCT SUMMARY				
COMPONENT	I _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)
TSAL5300	45	± 22	940	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSAL5300	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		
TSAL5300-MSZ	Tape and ammopack	MOQ: 5000 pcs, 1000 pcs/ammopack	T-1¾		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	5	V
Forward current		I _F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	200	mA
Surge forward current	t _p = 100 μs	I _{FSM}	1.5	Α
Power dissipation		P _V	160	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 85	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W

Note

T_{amb} = 25 °C, unless otherwise specified

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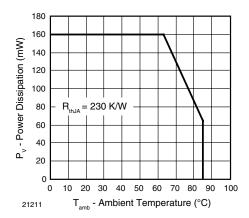


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

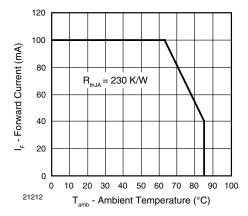


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.35	1.6	V
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V _F		2.6	3	V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		25		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	le	30	45	150	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	l _e	260	350		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe		35		mW
Temperature coefficient of φ _e	I _F = 20 mA	ТКφе		- 0.6		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I _F = 100 mA	λ_{p}		940		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Temperature coefficient of λ_p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		800		ns
	I _F = 1 A	t _r		500		ns
Fall time	I _F = 100 mA	t _f		800		ns
	I _F = 1 A	t _f		500		ns
Virtual source diameter	Method: 63 % encircled energy	d		2.3		mm

Note

 T_{amb} = 25 °C, unless otherwise specified



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BASIC CHARACTERISTICS

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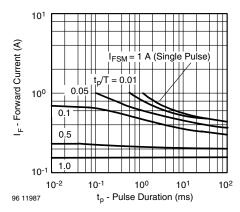


Fig. 3 - Pulse Forward Current vs. Pulse Duration

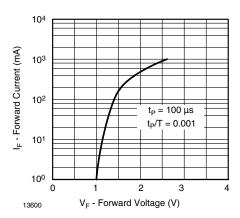


Fig. 4 - Forward Current vs. Forward Voltage

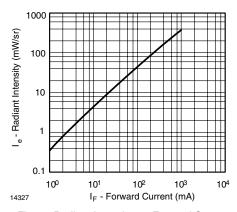


Fig. 5 - Radiant Intensity vs. Forward Current

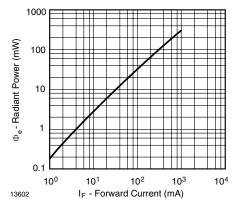


Fig. 6 - Radiant Power vs. Forward Current

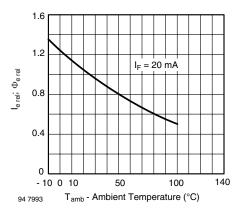


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

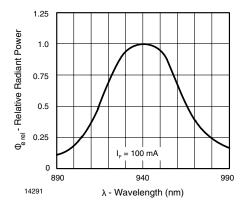


Fig. 8 - Relative Radiant Power vs. Wavelength

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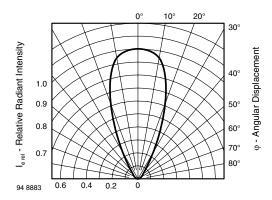
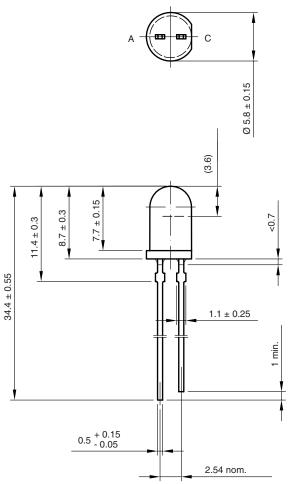
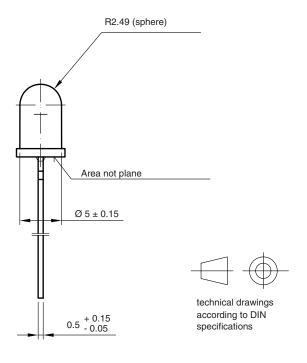


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters





6.544-5258.05-4 Issue: 8; 19.05.09 96 12122



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TAPE DIMENSIONS TSAL5300				
OPTION	H ± 0.5 mm	QUANTITY/BOX		
CS21Z	22	1000		
FSZ	27	1000		
GSZ	29	1000		
MSZ	25.5	1000		

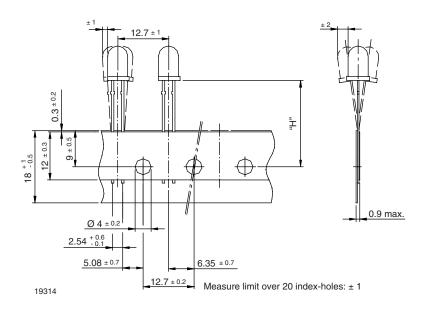


Fig. 10 - Ø 5 mm Devices on Tape

AMMOPACK

The tape is folded in a concertina arrangement and laid in cardboard box.

If components are required with cathode before the anode (figure 12), then start of tape should be taken from the side of the box marked "-". If components are required with anode before cathode, then tape should be taken from the side of the box marked "+".

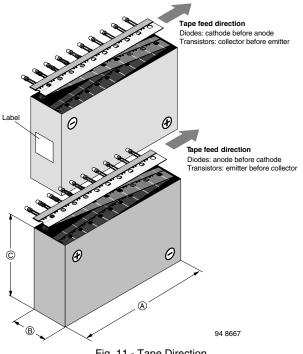


Fig. 11 - Tape Direction





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Revision: 11-Mar-11